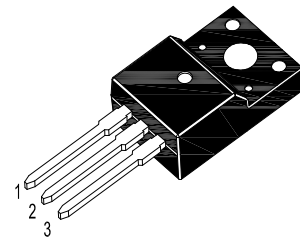
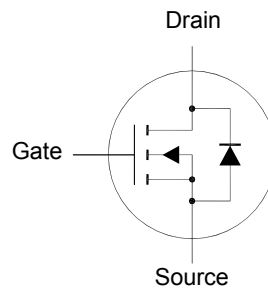


SFTN2906

N-Channel Enhancement Mode Power MOSFET



TO-220F Plastic Package
1.Gate 2.Drain 3.Source

Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---------------------------------------------------------------------------------|----------------|-------------------------------------------------------------------|------------------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current at $V_{GS} = 10\text{ V}$ | I_D | $T_C = 25^\circ\text{C}$ 84 $T_C = 100^\circ\text{C}$ 59 | A |
| Peak Drain Current | I_{DM} | $T_C = 25^\circ\text{C}$ 336 | A |
| Power Dissipation | P_{tot} | $T_C = 25^\circ\text{C}$ 38 | W |
| Single Pulse Avalanche energy at $I_D = 84\text{ A}$, $R_{GS} = 25\ \Omega$ | E_{AS} | 140 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |

Thermal Characteristics

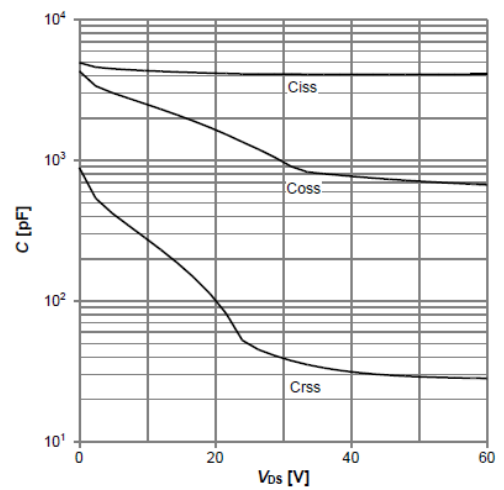
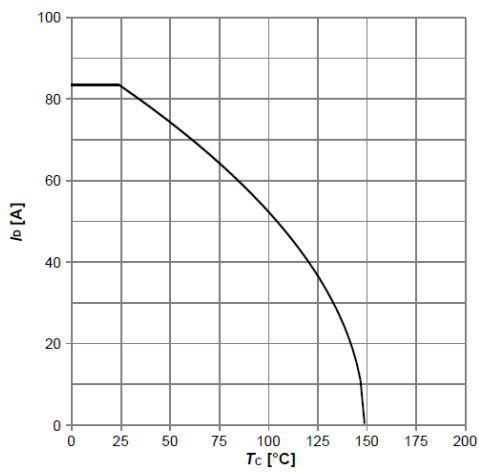
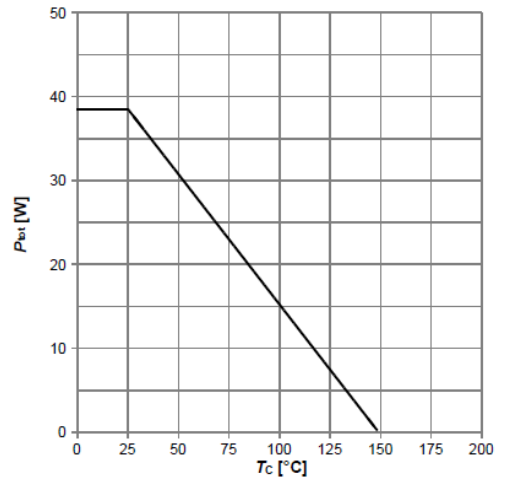
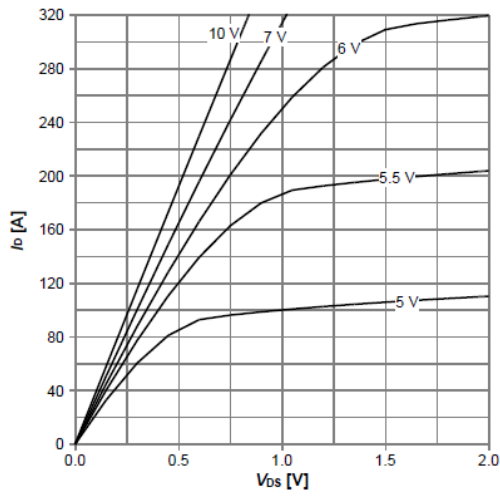
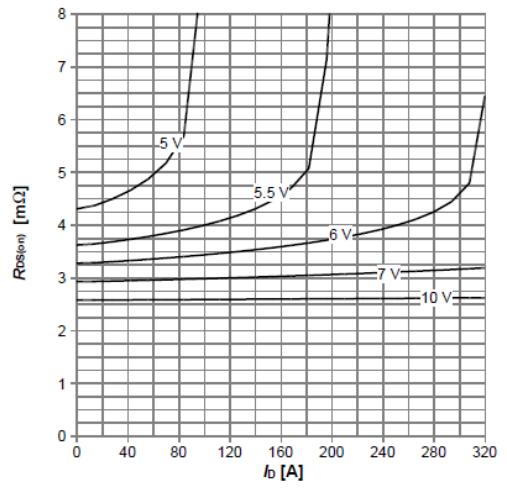
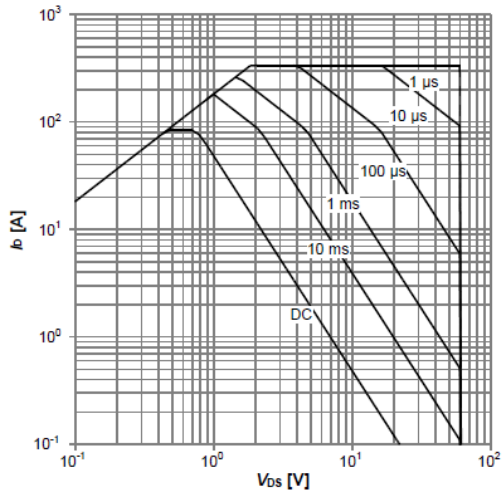
| Parameter | Symbol | Max. | Unit |
|--------------------------------------------------|-----------------|------|------|
| Maximum Thermal Resistance from Junction to Case | $R_{\theta JC}$ | 3.9 | K/W |

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Characteristics at $T_J = 25^\circ\text{C}$ unless otherwise specified

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|---------------------------------------------------------------------------------------------------------------------------------|--------------|--------|--------|------------|------------------|
| Drain-Source Breakdown Voltage at $I_D = 1\text{ mA}$ | BV_{DSS} | 60 | - | - | V |
| Drain-Source Leakage Current at $V_{DS} = 60\text{ V}$ at $V_{DS} = 60\text{ V}, T_J = 125^\circ\text{C}$ | I_{DSS} | - - | - - | 1 100 | μA |
| Gate Leakage Current at $V_{GS} = 20\text{ V}$ | I_{GSS} | - | - | 100 | nA |
| Gate-Source Threshold Voltage at $V_{DS} = V_{GS}, I_D = 75\ \mu\text{A}$ | $V_{GS(th)}$ | 2.1 | - | 3.3 | V |
| Drain-Source On-State Resistance at $V_{GS} = 10\text{ V}, I_D = 84\text{ A}$ at $V_{GS} = 6\text{ V}, I_D = 21\text{ A}$ | $R_{DS(on)}$ | - - | - - | 2.9 3.5 | $\text{m}\Omega$ |
| Forward Transconductance at $V_{DS} > 2I_D \cdot R_{DS(on)max}, I_D = 84\text{ A}$ | $ g_{FS} $ | 75 | 150 | - | S |
| Diode Forward Voltage at $I_F = 32\text{ A}, V_{GS} = 0\text{ V}$ | V_{SD} | - | - | 1.2 | V |
| Input Capacitance at $V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$ | C_{iss} | - | 4100 | - | pF |
| Output Capacitance at $V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$ | C_{oss} | - | 980 | - | pF |
| Reverse Transfer Capacitance at $V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$ | C_{rss} | - | 39 | - | pF |
| Turn-On Delay Time at $I_D = 84\text{ A}, V_{DD} = 30\text{ V}, V_{GS} = 10\text{ V}, R_G = 3\ \Omega$ | $t_{d(on)}$ | - | 16 | - | ns |
| Turn-On Rise Time at $I_D = 84\text{ A}, V_{DD} = 30\text{ V}, V_{GS} = 10\text{ V}, R_G = 3\ \Omega$ | t_r | - | 15 | - | ns |
| Turn-Off Delay Time at $I_D = 84\text{ A}, V_{DD} = 30\text{ V}, V_{GS} = 10\text{ V}, R_G = 3\ \Omega$ | $t_{d(off)}$ | - | 30 | - | ns |
| Turn-Off Fall Time at $I_D = 84\text{ A}, V_{DD} = 30\text{ V}, V_{GS} = 10\text{ V}, R_G = 3\ \Omega$ | t_f | - | 11 | - | ns |

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TO-220F Package Outline

